

# TrenchMV™ Power MOSFET

## IXTC200N10T

$V_{DSS} = 100V$   
 $I_{D25} = 101A$   
 $R_{DS(on)} \leq 6.3m\Omega$

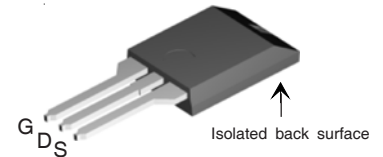
(Electrically Isolated Back Surface)

N-Channel Enhancement Mode  
Avalanche Rated



Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $175^\circ C$	100	V
$V_{DGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$	100	V
$V_{GSM}$	Transient	$\pm 30$	V
$I_{D25}$	$T_C = 25^\circ C$	101	A
$I_{LRMS}$	Lead Current Limit, RMS	75	A
$I_{DM}$	$T_C = 25^\circ C$ , pulse width limited by $T_{JM}$	500	A
$I_A$	$T_C = 25^\circ C$	40	A
$E_{AS}$	$T_C = 25^\circ C$	1.5	J
$P_D$	$T_C = 25^\circ C$	160	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	1.6mm (0.062in.) from case for 10s Plastic body for 10 seconds	300 260	$^\circ C$ $^\circ C$
$V_{ISOL}$	50/60Hz, $t = 1$ minute, $I_{ISOL} < 1mA$ , RMS	2500	V
$M_d$	Mounting force	11..65 / 2.5..14.6	N/lb.
<b>Weight</b>	ISOPLUS220	2	g

ISOPLUS220  
E153432



G = Gate  
S = Source  
D = Drain

### Features

- Silicon chip on Direct-Copper Bond (DCB) substrate
- Isolated mounting surface
- 2500V electrical isolation

### Advantages

- Easy to mount
- Space savings
- High power density

### Applications

- Automotive
  - Motor Drives
  - High Side Switch
  - 12V Battery
  - ABS Systems
- DC/DC Converters and Off-line UPS
- Primary - Side Switch
- High Current Switching Applications

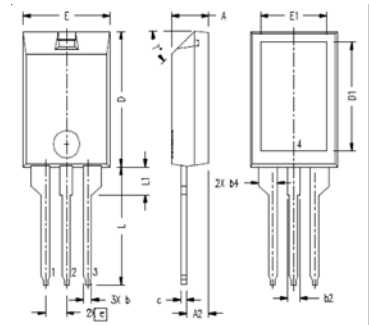
Symbol	Test Conditions ( $T_J = 25^\circ C$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0V$ $T_J = 150^\circ C$			5 $\mu A$ 250 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 50A$ , Notes 1			6.3 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1	60	96	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		9400	pF
$C_{oss}$			1087	pF
$C_{rss}$			140	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 50\text{A}$ $R_G = 3.3\Omega$ (External)		35	ns
$t_r$			31	ns
$t_{d(off)}$			45	ns
$t_f$			34	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 50\text{A}$		152	nC
$Q_{gs}$			47	nC
$Q_{gd}$			47	nC
$R_{thJC}$			0.96	$^\circ\text{C/W}$
$R_{thCH}$		0.21		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			200 A
$I_{SM}$	Repetitive, Pulse width limited by $T_{JM}$			500 A
$V_{SD}$	$I_F = 50\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			1.0 V
$t_{rr}$	$I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ , $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 50\text{V}$		76	ns
$Q_{RM}$			205	nC
$I_{RM}$			5.4	A

### ISOPLUS220 (IXTC) Outline



1. Gate 2. Drain  
3. Source

Note: Bottom heatsink (Pin 4) is electrically isolated from Pins 1, 2 and 3.

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.157	.197	4.00	5.00
A2	.098	.118	2.50	3.00
b	.035	.051	0.90	1.30
b2	.049	.065	1.25	1.65
b4	.093	.100	2.35	2.55
c	.028	.039	0.70	1.00
D	.591	.630	15.00	16.00
D1	.472	.512	12.00	13.00
E	.394	.433	10.00	11.00
E1	.295	.335	7.50	8.50
e	.100 BASIC		2.55 BASIC	
L	.512	.571	13.00	14.50
L1	.118	.138	3.00	3.50
T*			42.5*	47.5*

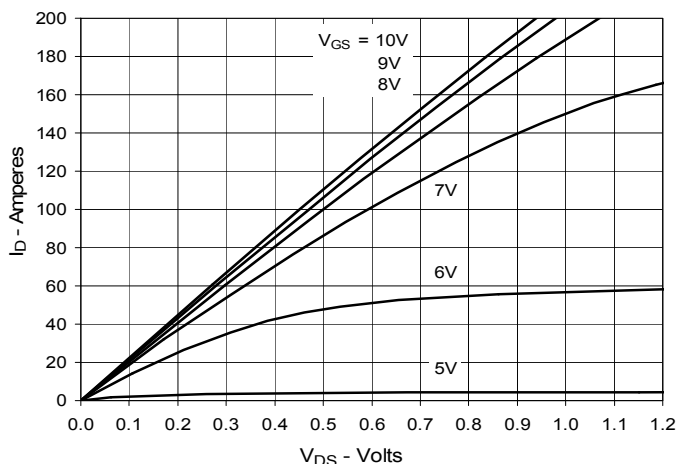
Notes: 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .

IXYS reserves the right to change limits, test conditions, and dimensions.

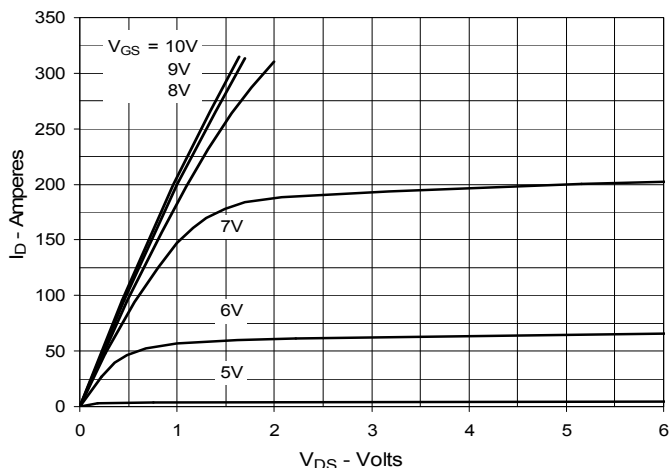
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

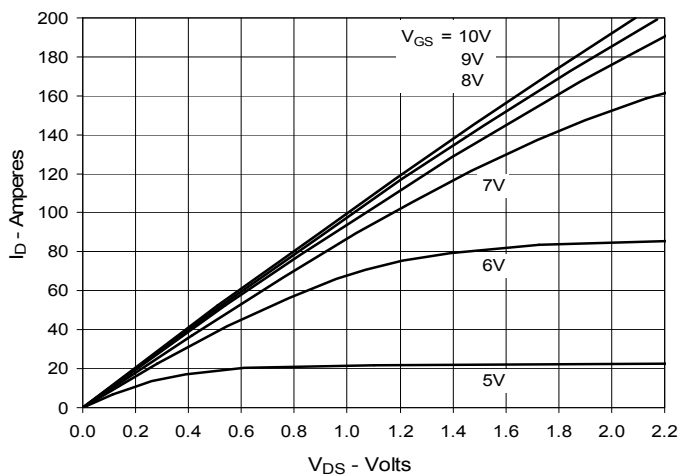
**Fig. 1. Output Characteristics @ 25°C**



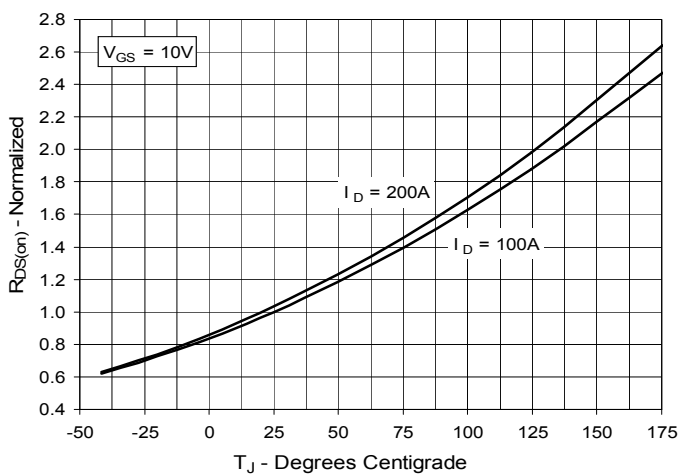
**Fig. 2. Extended Output Characteristics @ 25°C**



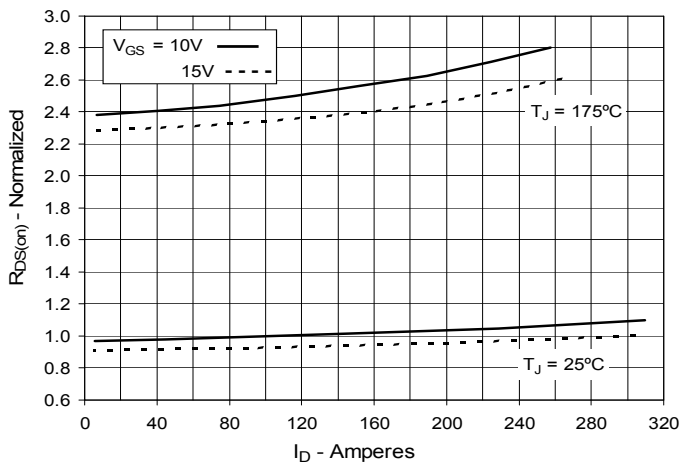
**Fig. 3. Output Characteristics @ 150°C**



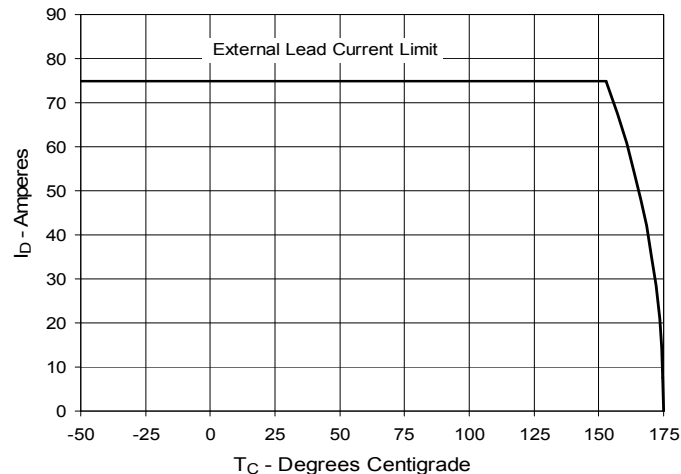
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 100A$  Value vs. Junction Temperature**



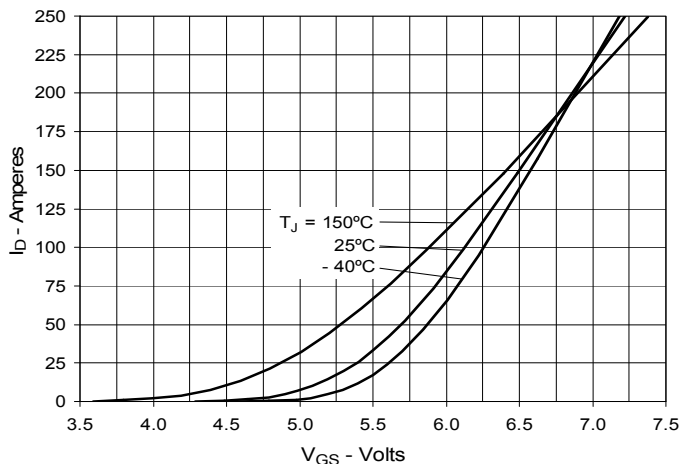
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 100A$  Value vs. Drain Current**



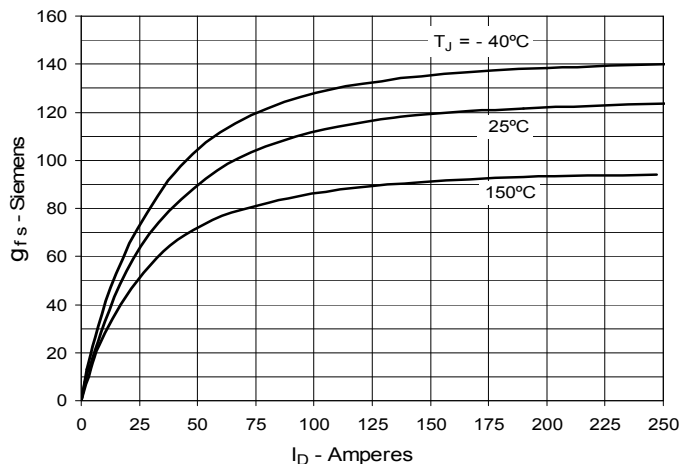
**Fig. 6. Drain Current vs. Case Temperature**



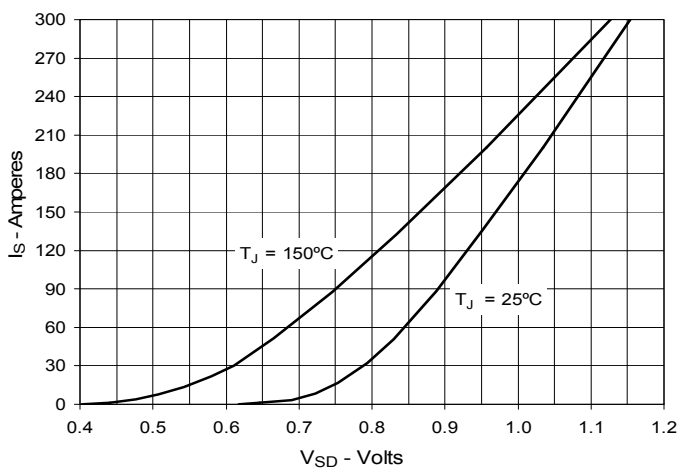
**Fig. 7. Input Admittance**



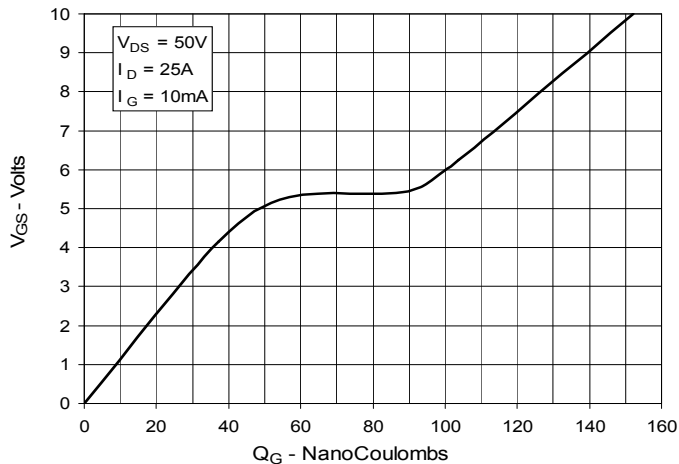
**Fig. 8. Transconductance**



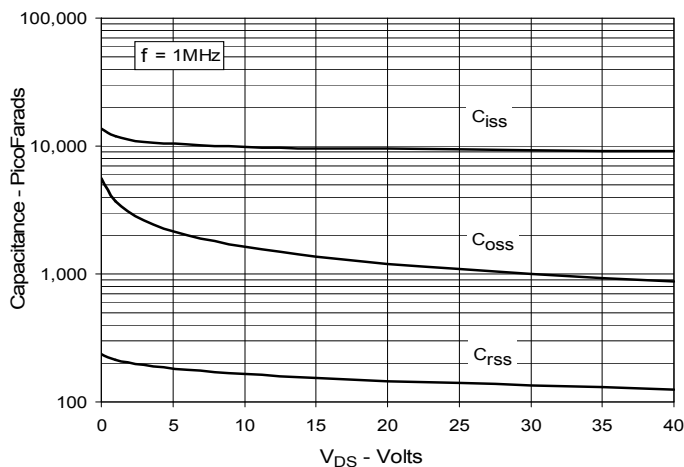
**Fig. 9. Forward Voltage Drop of Intrinsic Diode**



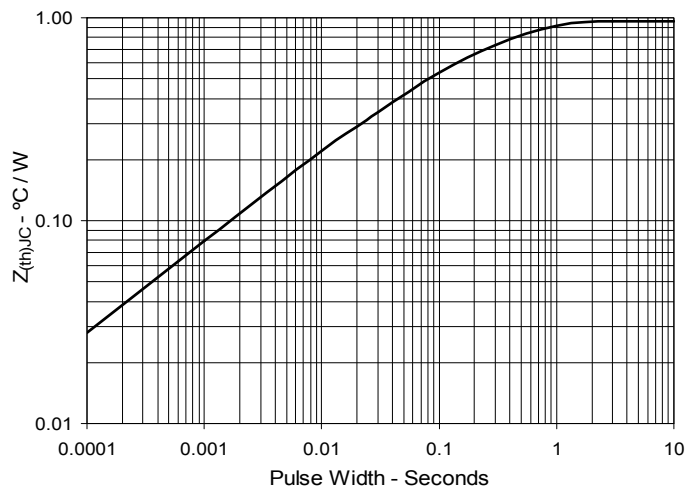
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**

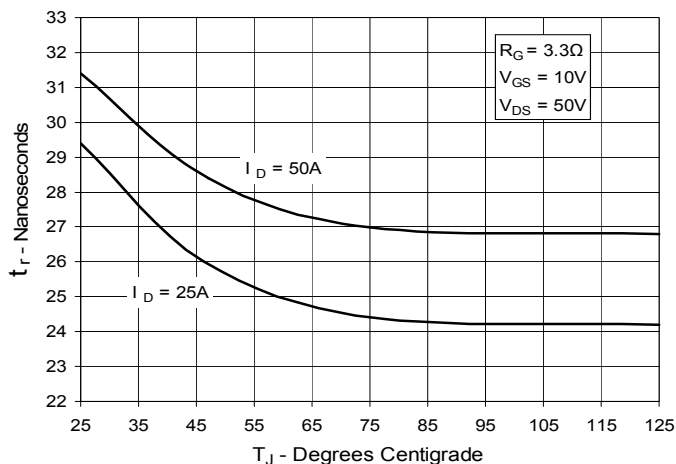


**Fig. 12. Maximum Transient Thermal Impedance**

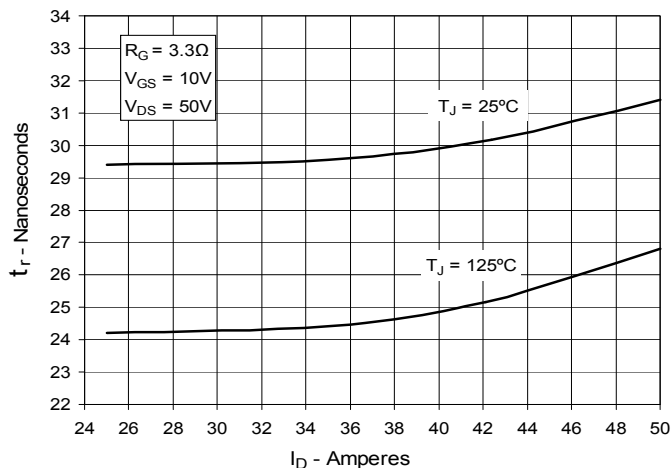


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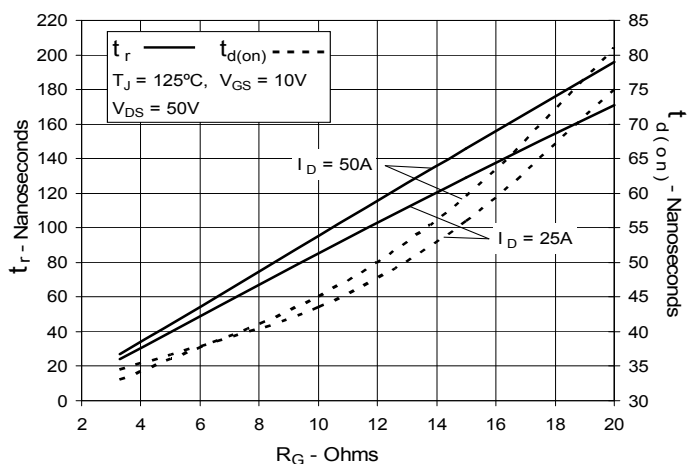
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



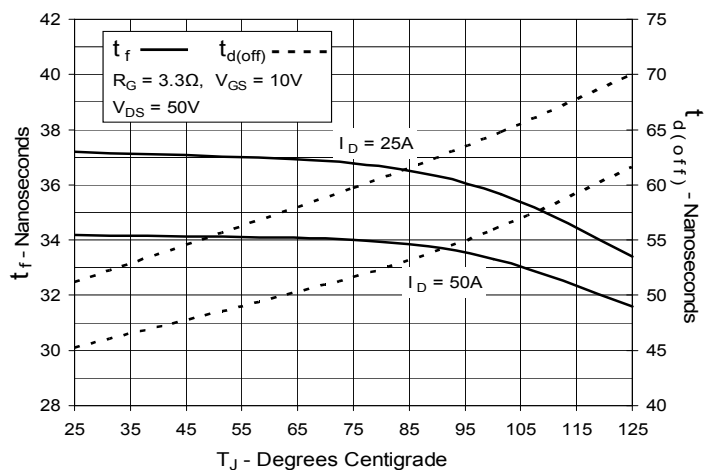
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



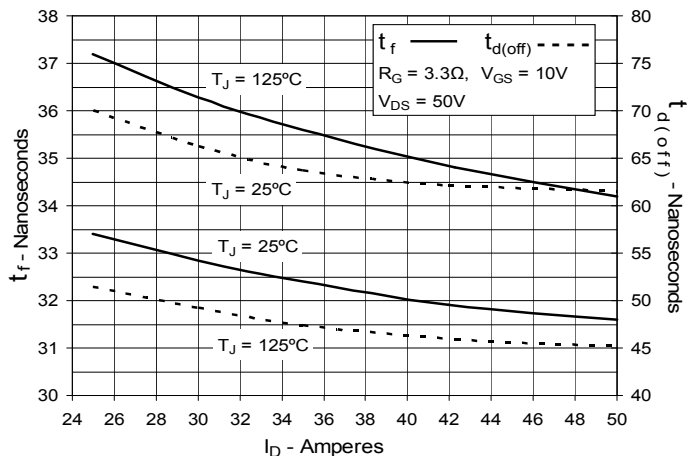
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

